

isc N-Channel MOSFET Transistor

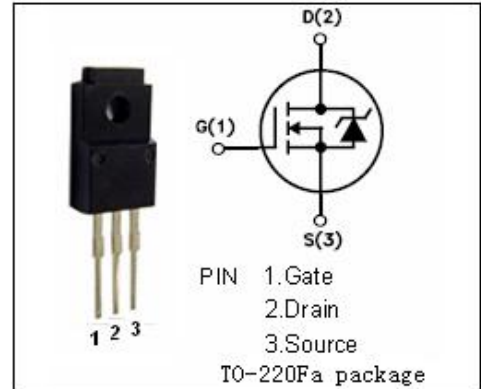
2SK988

DESCRIPTION

- Drain Current  $-I_D=10A @ T_C=25^\circ C$
- Drain Source Voltage-  
:  $V_{DSS}= 500V(\text{Min})$

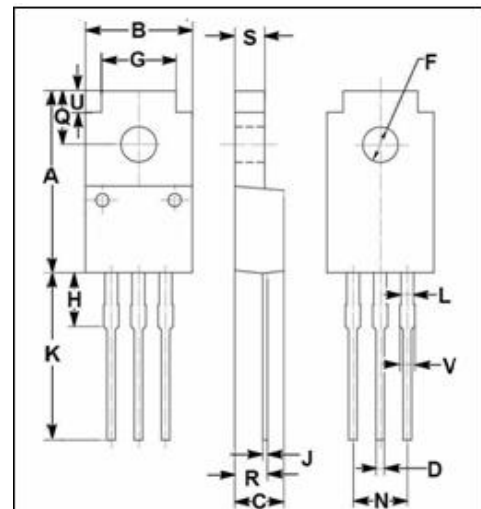
APPLICATIONS

- Designed for high voltage, high speed power switching



ABSOLUTE MAXIMUM RATINGS( $T_a=25^\circ C$ )

SYMBOL	PARAMETER	VALUE	UNIT
$V_{DSS}$	Drain-Source Voltage ( $V_{GS}=0$ )	500	V
$V_{GS}$	Gate-Source Voltage	$\pm 20$	V
$I_D$	Drain Current-continuous@ $T_C=25^\circ C$	10	A
$P_{tot}$	Total Dissipation@ $T_C=25^\circ C$	45	W
$T_j$	Max. Operating Junction Temperature	150	$^\circ C$
$T_{stg}$	Storage Temperature Range	-55~150	$^\circ C$



DIM	mm	
	MIN	MAX
A	16.85	17.15
B	9.90	10.10
C	4.35	4.65
D	0.75	0.80
F	3.20	3.40
G	6.90	7.10
H	5.15	5.45
J	0.45	0.75
K	13.35	13.65
L	1.10	1.30
N	4.98	5.18
Q	4.85	5.15
R	2.95	3.25
S	2.70	2.90
U	1.75	2.05
V	1.30	1.50

THERMAL CHARACTERISTICS

SYMBOL	PARAMETER	MAX	UNIT
$R_{th j-c}$	Thermal Resistance, Junction to Case	0.83	$^\circ C/W$
$R_{th j-a}$	Thermal Resistance, Junction to Ambient	35	$^\circ C/W$

**isc N-Channel Mosfet Transistor****2SK988****• ELECTRICAL CHARACTERISTICS (T<sub>C</sub>=25°C)**

SYMBOL	PARAMETER	CONDITIONS	MIN	TYP	MAX	UNIT
V <sub>(BR)DSS</sub>	Drain-Source Breakdown Voltage	V <sub>GS</sub> =0; I <sub>D</sub> = 10mA	500			V
V <sub>GS(th)</sub>	Gate Threshold Voltage	V <sub>DS</sub> =0; I <sub>D</sub> =1mA	2.0		4.0	V
R <sub>DS(on)</sub>	Drain-Source On-stage Resistance	V <sub>GS</sub> =10V; I <sub>D</sub> =5A			0.9	Ω
I <sub>GSS</sub>	Gate Source Leakage Current	V <sub>GS</sub> = ±20V; V <sub>DS</sub> = 0			± 100	nA
I <sub>DSS</sub>	Zero Gate Voltage Drain Current	V <sub>DS</sub> =500V; V <sub>GS</sub> = 0			500	uA